

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Canceled)
2. (New) A semiconductor device comprising:
a plurality of pixels over a substrate;
a data line driver circuit over the substrate; and
a dividing circuit over the substrate,
wherein the dividing circuit divides a signal into n signals, and
wherein the n signals are inputted into corresponding n pixels by a timing signal
supplied from the data driver circuit, simultaneously.
3. (New) A semiconductor device comprising:
a plurality of pixels over a substrate;
a data line driver circuit comprising a plurality of NAND circuits over the
substrate; and
a dividing circuit over the substrate,
wherein the dividing circuit divides a signal into n signals, and
wherein the n signals are inputted into corresponding n pixels by a timing signal
supplied from one of the plurality of NAND circuits, simultaneously.
4. (New) A semiconductor device comprising:
a plurality of pixels over a substrate;
a data line driver circuit over the substrate;
a dividing circuit over the substrate;

wherein the dividing circuit divides three signals corresponding to colors R, G and B into $3n$ signals,

wherein the $3n$ signals are inputted into corresponding $3n$ pixels by a timing signal supplied from the data driver circuit, simultaneously.

5. (New) A semiconductor device comprising:

a plurality of pixels over a substrate;

a data line driver circuit comprising a plurality of NAND circuits over the substrate; and

a dividing circuit over the substrate,

wherein the dividing circuit divides three signals corresponding to colors R, G and B into $3n$ signals, and

wherein the $3n$ signals are inputted into corresponding $3n$ pixels by a timing signal supplied from one of the plurality of NAND circuits, simultaneously.

6. (New) A semiconductor device comprising:

a plurality of pixels over a substrate, each of the plurality of pixels having a thin film transistor;

a data line driver circuit over the substrate; and

a dividing circuit over the substrate,

wherein the dividing circuit divides a signal into n signals, and

wherein the n signals are inputted into thin film transistors corresponding n pixels by a timing signal supplied from the data driver circuit, simultaneously.

7. (New) A semiconductor device comprising:

a plurality of pixels over a substrate, each of the plurality of pixels having a thin film transistor;

a data line driver circuit comprising a plurality of NAND circuits over the substrate; and

a dividing circuit over the substrate,

wherein the dividing circuit divides a signal into n signals, and

wherein the n signals are inputted into thin film transistors corresponding to n pixels by a timing signal supplied from one of the plurality of NAND circuits, simultaneously.

8. (New) A semiconductor device comprising:

a plurality of pixels over a substrate, each of the plurality of pixels having a thin film transistor;

a data line driver circuit over the substrate;

a dividing circuit over the substrate;

wherein the dividing circuit divides three signals corresponding to colors R, G and B into $3n$ signals,

wherein the $3n$ signals are inputted into thin film transistors corresponding to $3n$ pixels by a timing signal supplied from the data driver circuit, simultaneously.

9. (New) A semiconductor device comprising:

a plurality of pixels over a substrate, each of the plurality of pixels having a thin film transistor;

a data line driver circuit comprising a plurality of NAND circuits over the substrate; and

a dividing circuit over the substrate,

wherein the dividing circuit divides three signals corresponding to colors R, G and B into $3n$ signals, and

wherein the $3n$ signals are inputted into thin film transistors corresponding to $3n$ pixels by a timing signal supplied from one of the plurality of NAND circuits, simultaneously.

10. (New) A semiconductor device according to claim 2, wherein the data line driver circuit comprises a shift register, NAND circuits, a level shifter and a buffer.

11. (New) A semiconductor device according to claim 3, wherein the data line driver circuit further comprises a shift register, a level shifter and a buffer.

12. (New) A semiconductor device according to claim 4, wherein the data line driver circuit comprises a shift register, NAND circuits, a level shifter and a buffer.

13. (New) A semiconductor device according to claim 5, wherein the data line driver circuit further comprises a shift register, a level shifter and a buffer.

14. (New) A semiconductor device according to claim 6, wherein the data line driver circuit comprises a shift register, NAND circuits, a level shifter and a buffer.

15. (New) A semiconductor device according to claim 7, wherein the data line driver circuit further comprises a shift register, a level shifter and a buffer.

16. (New) A semiconductor device according to claim 8, wherein the data line driver circuit comprises a shift register, NAND circuits, a level shifter and a buffer.

17. (New) A semiconductor device according to claim 9, wherein the data line driver circuit further comprises a shift register, a level shifter and a buffer.

18. (New) A semiconductor device according to claim 2, wherein the substrate comprises glass.

19. (New) A semiconductor device according to claim 3, wherein the substrate comprises glass.

20. (New) A semiconductor device according to claim 4, wherein the substrate comprises glass.

21. (New) A semiconductor device according to claim 5, wherein the substrate comprises glass.

22. (New) A semiconductor device according to claim 6, wherein the substrate comprises glass.

23. (New) A semiconductor device according to claim 7, wherein the substrate comprises glass.

24. (New) A semiconductor device according to claim 8, wherein the substrate comprises glass.

25. (New) A semiconductor device according to claim 9, wherein the substrate comprises glass.

26. (New) A semiconductor device according to claim 6, wherein the thin film transistor comprises polycrystalline silicon film.

27. (New) A semiconductor device according to claim 7, wherein the thin film transistor comprises polycrystalline silicon film.

28. (New) A semiconductor device according to claim 8, wherein the thin film transistor comprises polycrystalline silicon film.

29. (New) A semiconductor device according to claim 9, wherein the thin film transistor comprises polycrystalline silicon film.

30. (New) A semiconductor device according to claim 2, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

31. (New) A semiconductor device according to claim 3, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

32. (New) A semiconductor device according to claim 4, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

33. (New) A semiconductor device according to claim 5, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

34. (New) A semiconductor device according to claim 6, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

35. (New) A semiconductor device according to claim 7, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

36. (New) A semiconductor device according to claim 8, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.

37. (New) A semiconductor device according to claim 9, wherein the semiconductor device is applied to an electric apparatus selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle type

display, a player apparatus which is equipped with a recording medium for recording a program and a digital camera.